

## **Description**

The SM4305PSKPC-TRG uses advanced trench technology excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as aload switch or in PWM applications.

### **General Features**

 $V_{DS} = -30V, I_{D} = -50A$ 

 $R_{DS(ON)}$  < 15m $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)}$  < 25m $\Omega$  @  $V_{GS}$ =-4.5V

High Power and current handing capability

Lead free product is acquired

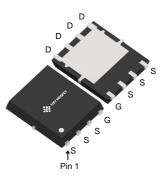
Surface mount package

#### **Application**

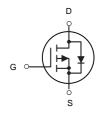
PWM applications

Load switch

Power management



DFN5X6-8L (DFN-8-EP(5.8x5.3))



P-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
SM4305PSKPC-TRG	DFN5X6-8L(DFN-8-EP(5.8x5.3))	HXY MOSFET	5000

### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
VDS	Drain-Source Voltage	-30	V	
VGS	Gate-Source Voltage	±20	V	
	Drain Current-Continuous (Tc=25 ℃)	-50	_	
lD	Drain Current-Continuous (Tc=100℃)	-24	Α	
IDM	Drain Current-Pulsed (Note 1)	-80	А	
_	Maximum Power Dissipation (T <sub>C</sub> =25 °C)	3	W	
P <sub>D</sub>	Maximum Power Dissipation (T <sub>C</sub> =100℃)	1.3		
EAS	Single pulse avalanche energy (Note 5)	231	mJ	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C	
RθJA	Thermal Resistance,Junction-to-Ambient (Note 2)	41.67	°C/W	

### P-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

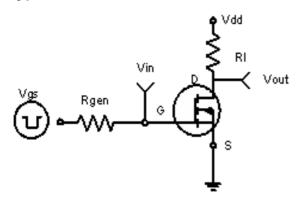
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	IGSS	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.5	-3	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	9	15	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-7A	-	18	25	mΩ
Forward Transconductance	gFS	V <sub>DS</sub> =-10V,I <sub>D</sub> =-10A	-	20	-	S
Input Capacitance	Clss		-	1750	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	215	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	180	-	PF
Turn-on Delay Time	td(on)		-	9	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V, ID=-10A,	-	8	-	nS
Turn-Off Delay Time	td(off)	V <sub>GS</sub> =-10V,R <sub>GEN</sub> =1Ω	-	28	-	nS
Turn-Off Fall Time	tf		-	10	-	nS
Total Gate Charge	Qg		-	24	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-10A,V <sub>GS</sub> =- 10V	-	3.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6	-	nC
Diode Forward Current (Note 2)	ls		-	-	-12	Α
Diode Forward Voltage (Note 3)	VSD	V <sub>GS</sub> =0V,I <sub>S</sub> =-12A	-	-	-1.2	V

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}$ C,V<sub>DD</sub>=-15V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$ , I<sub>AS</sub>=-34A



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

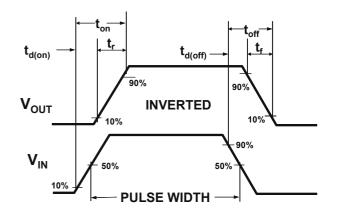
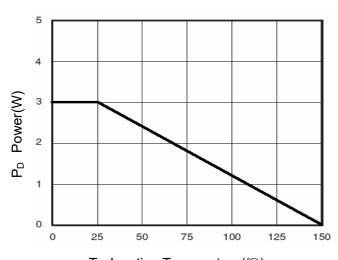


Figure 2:Switching Waveforms



 $T_J$ -Junction Temperature (°C) Figure 3 Power Dissipation

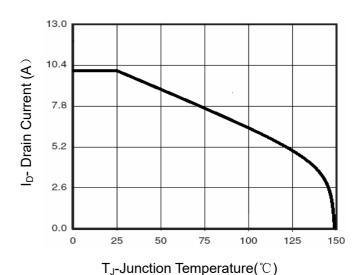
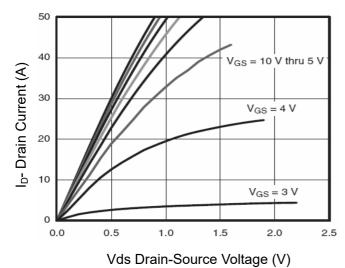


Figure 4 Drain Current



**Figure 5 Output Characteristics** 

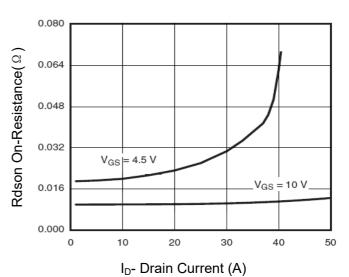
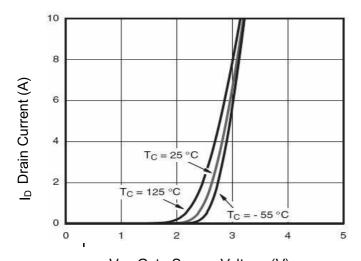


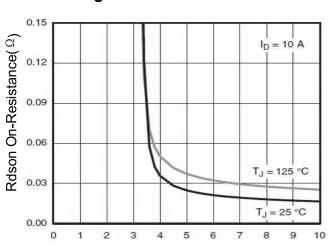
Figure 6 Drain-Source On-Resistance



### **Figure 5 Output Characteristics**



Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

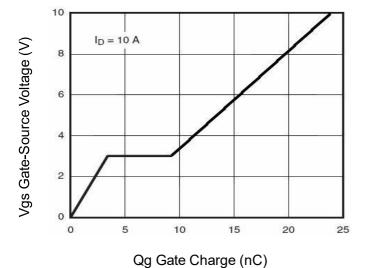


Figure 11 Gate Charge

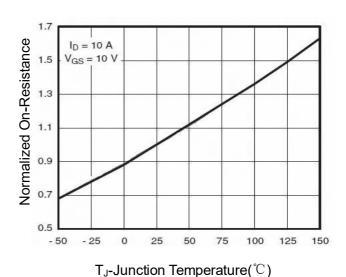
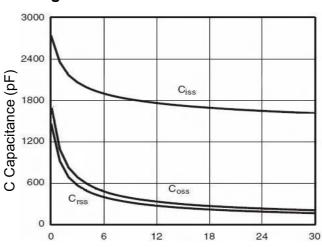


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds

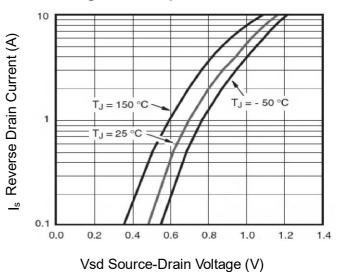
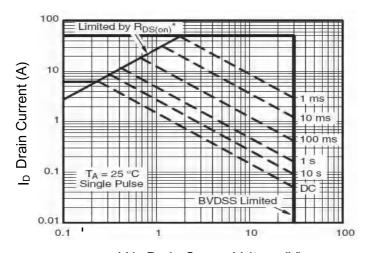


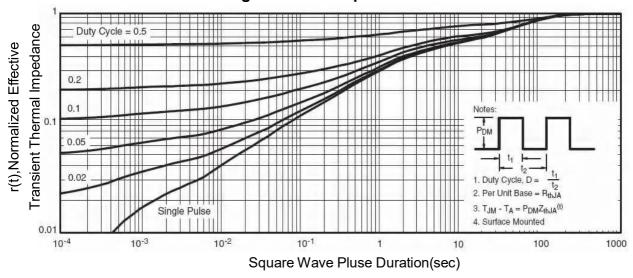
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

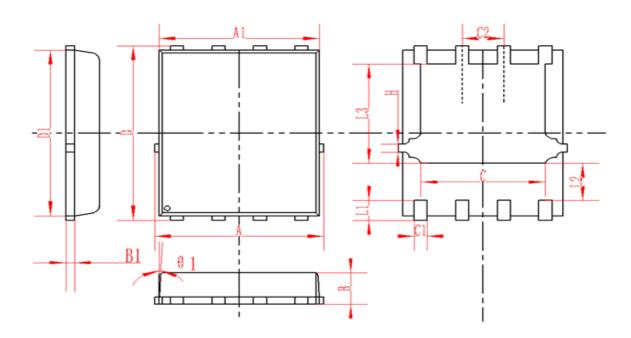
Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# DFN5X6-8L(DFN-8-EP(5.8x5.3)) Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP		0.5TYP			
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Η	0.24	0.25	0.26	0.009	0.010	0.010

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